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Journal Information

Journal Title	Microelectronic Engineering
Publisher	Elsevier B.V.
ISSN	0167-9317
E-ISSN	
Database	SCOPUS
Domain	Physical Sciences, Social Sciences

Classification History

Year	A+	A	B	C
2026		✓	✓	
2025		✓	✓	
2024		✓	✓	
2023		✓	✓	
2021/2022		✓	✓	
2020		✓	✓	
2019		✓	✓	
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